

**INTEGRATED CIRCUIT FERROELECTRIC MEMORY DEVICES  
INCLUDING PLATE LINES DIRECTLY ON FERROELECTRIC  
CAPACITORS AND METHODS OF FABRICATING THE SAME**

**Abstract of the Disclosure**

Integrated circuit ferroelectric memory devices are provided that include an integrated circuit transistor. The memory device further includes a ferroelectric capacitor on the integrated circuit transistor. The ferroelectric capacitor includes a first electrode adjacent the transistor, a second electrode remote from the transistor and a ferroelectric film therebetween. The memory device further includes a plate line directly on the ferroelectric capacitor. Methods are also provided that include forming a ferroelectric capacitor on the integrated circuit transistor and forming a plate line directly on the ferroelectric capacitor.